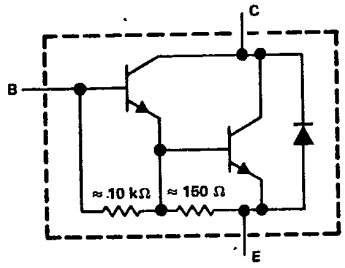
TIP620, TIP621, TIP622
N-P-N DARLINGTON-CONNECTED SILICON POWER TRANSISTORS

REVISED OCTOBER 1984

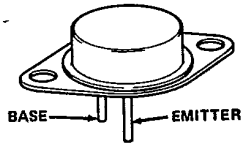
T-33-29

- Designed For Complementary use with TIP625, TIP626, TIP627
- 65 W at 25°C Case Temperature
- 5 A Rated Collector Current
- Min h_{FE} of 1000 at 3 V, 3 A
- 50 mJ Reverse Energy Rating

device schematic



TO-3 PACKAGE



THE COLLECTOR IS IN ELECTRICAL CONTACT WITH THE CASE

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	TIP620	TIP621	TIP622
Collector-base voltage	60 V	80 V	100 V
Collector-emitter voltage (I_B = 0)	60 V	80 V	100 V
Emitter-base voltage	5 V		
Continuous collector current	5 A		
Peak collector current (see Note 1)	8 A		
Continuous base current	0.1 A		
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)	65 W		
Continuous device dissipation at (or below) 25°C free-air temperature (see Note 3)	4 W		
Unclamped inductive load energy (see Note 4)	50 mJ		
Operating collector junction and storage temperature range	−65°C to 200°C		
Lead temperature 3,2 mm (0.125 inch) from case for 10 seconds	260°C		

NOTES: 1. This value applies for $t_w \leq 0.3$ ms, duty cycle ≤ 10%.
2. Derate linearly to 200°C case temperature at the rate of 0.37 W/°C or refer to Dissipation Derating Curve, Figure 9.
3. Derate linearly to 200°C free-air temperature at the rate of 23 mW/°C or refer to Dissipation Derating Curve, Figure 10.
4. This rating is based on the capability of the transistor to operate safely in the circuit in Figure 2. L = 20 mH, R_{BB2} = 100 Ω, V_{BB2} = 0 V, R_S = 0.1 Ω, V_{CC} = 20 V. Energy ≈ $I_C^2L/2$.

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electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS		TIP620			TIP621			TIP622			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$V_{(BR)CEO}$	I_C = 30 mA, See Note 5	I_B = 0,	60			80			100			V
I_{CBO}	V_{CB} = 60 V,	I_E = 0			0.2							mA
	V_{CB} = 80 V,	I_E = 0						0.2				
	V_{CB} = 100 V,	I_E = 0									0.2	
I_{CEO}	V_{CE} = 30 V,	I_B = 0			0.50							mA
	V_{CE} = 40 V,	I_B = 0						0.5				
	V_{CE} = 50 V,	I_B = 0									0.5	
I_{EBO}	V_{EB} = 5 V,	I_C = 0			2			2			2	mA
h_{FE}	V_{CE} = 3 V, See Notes 5 and 6	I_C = 0.5 A,	1000			1000			1000			
	V_{CE} = 3 V, See Notes 5 and 6	I_C = 3 A,	1000			1000			1000			
V_{BE}	V_{CE} = 3 V, See Notes 5 and 6	I_C = 3 A,			2.5			2.5			2.5	V
$V_{CE(sat)}$	I_B = 12 mA, See Notes 5 and 6	I_C = 3 A,			2			2			2	V
	I_B = 20 mA, See Notes 5 and 6	I_C = 5 A,			4			4			4	
V_F	I_F = 5 A, See Notes 5 and 6				3.5			3.5			3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, t_w = 300 μs, duty cycle ≤ 2 %.
6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts located within 3,2 mm (0.125 inch) from the device body.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$			2.69	°C/W
$R_{\theta JA}$			43.75	

resistive-load switching characteristic at 25°C case temperature

PARAMETER	TEST CONDITIONS†				MIN	TYP	MAX	UNIT
t_{on}	I_C = 3 A,	I_{B1} = 12 mA,	I_{B2} = −12 mA,			1.5		μs
t_{off}	$V_{BE(off)}$ = −5 V,	R_L = 10 Ω,	See Figure 1			8.5		

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

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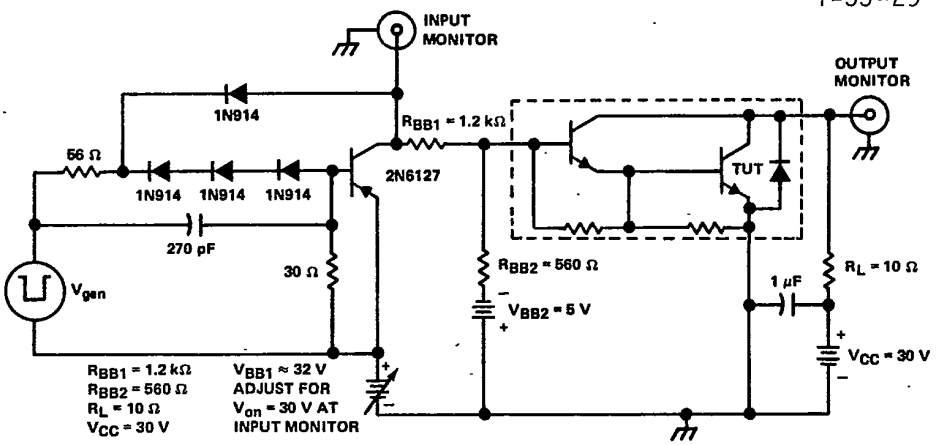
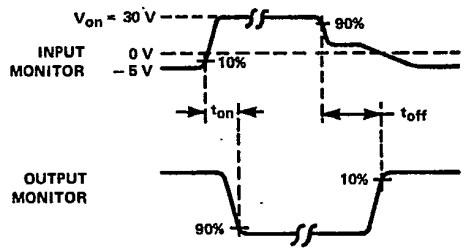
PARAMETER MEASUREMENT INFORMATION

T-33-29



TEST CIRCUIT



VOLTAGE WAVEFORMS

NOTES: A. V_{gen} is a −30-V pulse into a 50 Ω termination.
B. The V_{gen} waveform is supplied by a generator with the following characteristics: $t_r \leq 15$ ns, $t_f \leq 15$ ns, $Z_{out} = 50\ \Omega$, $t_w = 20\ \mu s$, duty cycle ≤ 2 %.
C. Waveforms are monitored on an oscilloscope with the following characteristics: $t_r \leq 15$ ns, $R_{in} \geq 10\ M\Omega$, $C_{in} \leq 11.5$ pF.
D. Resistors must be noninductive types.
E. The d-c power supplies may require additional bypassing in order to minimize ringing.

FIGURE 1. RESISTIVE-LOAD SWITCHING

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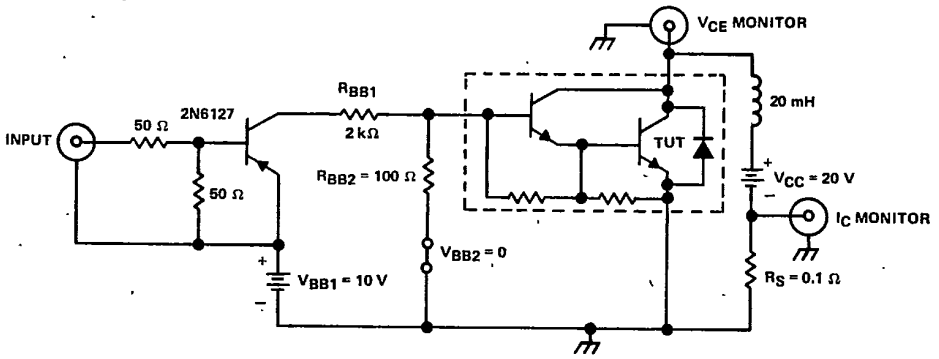
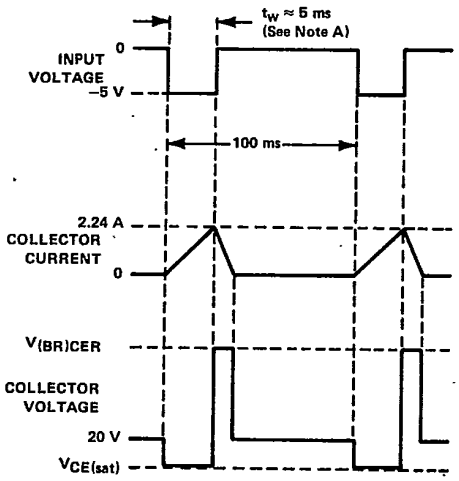
PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE AND CURRENT WAVEFORMS

NOTE A: Input pulse duration is increased until I_{CM} = 2.24 A.

FIGURE 2. INDUCTIVE-LOAD SWITCHING

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TYPICAL CHARACTERISTICS

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STATIC FORWARD CURRENT TRANSFER RATIO
vs
COLLECTOR CURRENT

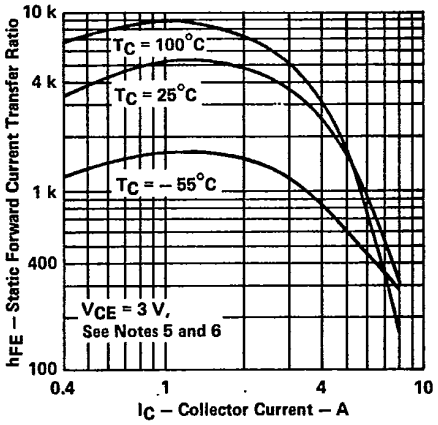

FIGURE 3

BASE-EMITTER VOLTAGE
vs
COLLECTOR CURRENT

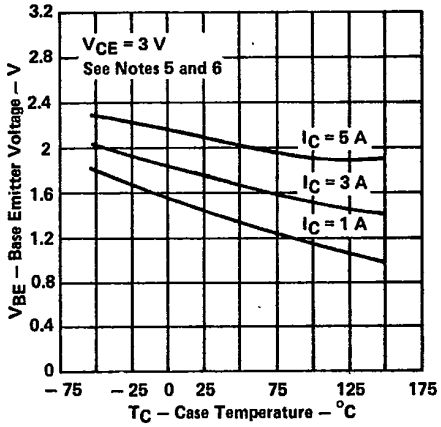

FIGURE 4

COLLECTOR-EMITTER SATURATION VOLTAGE
vs
COLLECTOR CURRENT

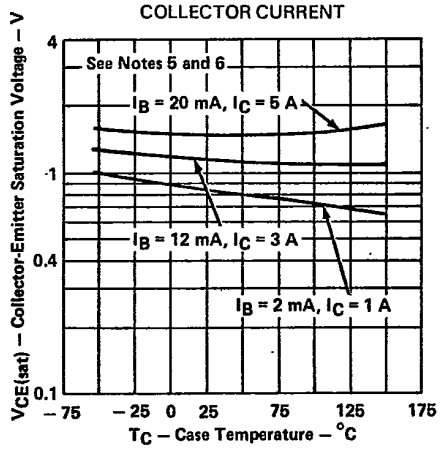

FIGURE 5

SMALL SIGNAL COMMON-EMITTER
FORWARD CURRENT TRANSFER RATIO
vs
FREQUENCY

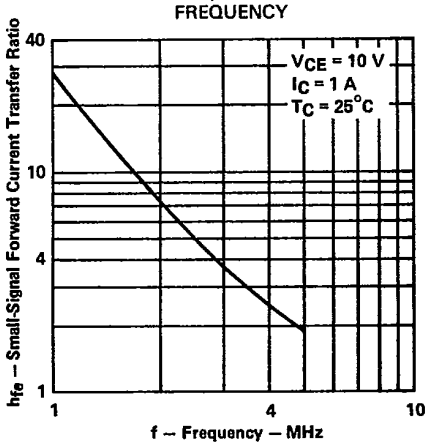

FIGURE 6

NOTES: 5. These parameters must be measured using pulse techniques, t_w = 300 μs, duty cycle ≤ 2 %.
6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts located within 3,2 mm (0.125 inch) from the device body.

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MAXIMUM SAFE OPERATING AREA

MAXIMUM COLLECTOR CURRENT
vs
COLLECTOR-EMITTER VOLTAGE

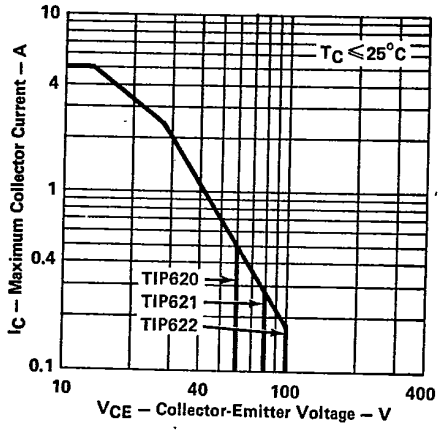

FIGURE 7

MAXIMUM COLLECTOR CURRENT
vs
UNCLAMPED INDUCTIVE LOAD

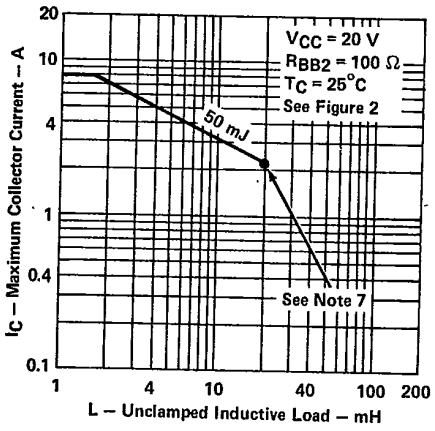

FIGURE 8

NOTE 7: Above this point the safe operating area has not been defined.

THERMAL INFORMATION

CASE TEMPERATURE
DISSIPATION DERATING CURVE

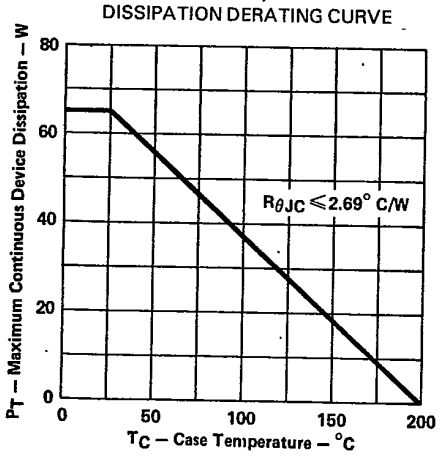

FIGURE 9

FREE-AIR TEMPERATURE
DISSIPATION DERATING CURVE

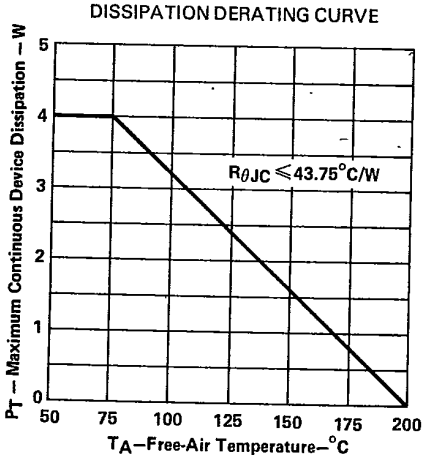

FIGURE 10

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